

## BC807-16W/25W/40W

TRANSISTOR (PNP)

#### **FEATURES**

- Ldeally suited for automatic insertion
- Epitaxial planar die construction
- Complementary to BC817W

### MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	<b>-</b> 50	٧	
V <sub>CEO</sub>	Collector-Emitter Voltage	Emitter Voltage -45		
V <sub>EBO</sub>	Emitter-Base Voltage	e Voltage -5		
Ic	Collector Current -Continuous	<b>-</b> 0.5	Α	
Pc	Collector Power Dissipation	0.2	W	
R <sub>θJA</sub>	Thermal Resistance from Junction to Ambient	625	°C/W	
T <sub>J</sub> ,T <sub>stg</sub>	Storage Temperature	-55~+150	°C	



### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> =-10μΑ,I <sub>E</sub> =0	-50		V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> =-10mA,I <sub>B</sub> =0	<b>-</b> 45		٧
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> =-1μΑ,I <sub>C</sub> =0	<b>-</b> 5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-20 V , I <sub>E</sub> =0		-0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5 V , I <sub>C</sub> =0		-0.1	μΑ
DC compant main	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1V,I <sub>C</sub> = -100mA	100	600	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> =-1V,I <sub>C</sub> = -500mA	40		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA,I <sub>B</sub> =-50 mA		-0.7	V
Base-emitter voltage	V <sub>BE(on)</sub>	V <sub>CE</sub> = -1V,I <sub>C</sub> = -500mA		-1.2	V
Transition frequency	f⊤	V <sub>CE</sub> =-5 V, I <sub>C</sub> = -10mA f=100MHz	80		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V,f=1MHz		10	pF

### CLASSIFICATION of hFE (1)

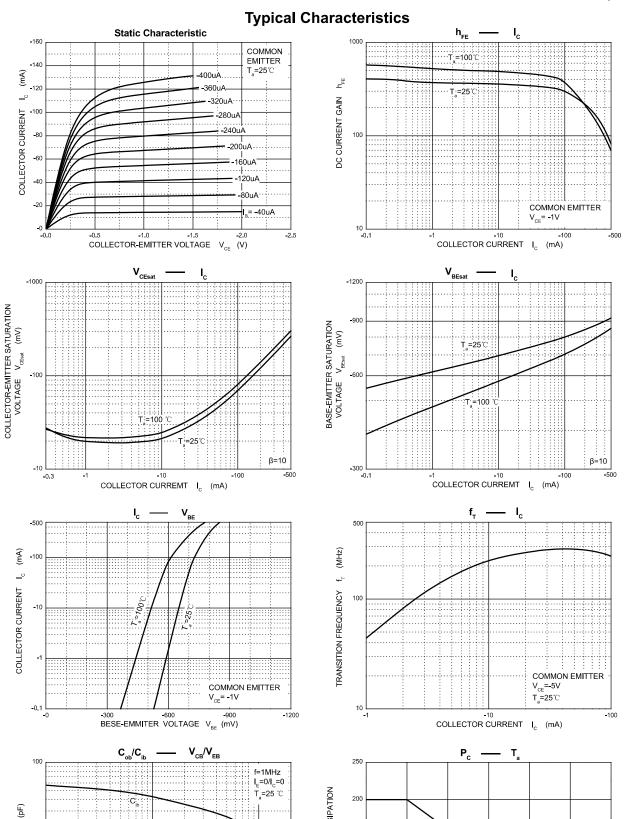
Rank	BC807-16W	BC807-25W	BC807-40W
Range	100-250	160-400	250-600
Marking	5A	5B	5C



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# BC807-16W/25W/40W

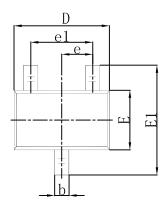
TRANSISTOR (PNP)

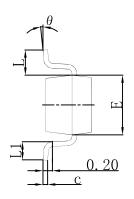


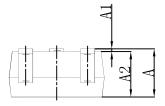
## BC807-16W/25W/40W

TRANSISTOR (PNP)

### **SOT-323 Package Outline Dimensions**

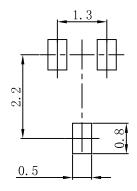






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650	) TYP	0.026	5 TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

### **SOT-323 Suggested Pad Layout**



#### Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

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